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Pending
Active
L9: (13) (((memory and redundan$2) and ((defect$3 adj3 address)
Failed
Saved
(96) (shift adj2 redundan$4) and defect$3 and memory
(40) (shift adj2 redundan$4) and (defect$3 adj3 (line bus connecti
(30) (shift adj2 redundan$4) and (defect$3 adj3 line) and memory
(1) ((shift adj2 redundan$4) and (defect$3 adj3 (line bus connecti
(10) ((shift adj2 redundan$4) and (defect$3 adj3 (line bus connecti
(12) ((shift adj2 redundan$4) and (defect$3 adj3 (line bus connecti
(47149) address near2 input
(US-6314033-S or US-6188597-S or US-5491655-S or US-6304501-S
(1) L63 and L64
(5) (address near2 input) and ((US-6314033-S or US-6188597-S or US-
(1880) (address near3 input) and redundant and defect$3
(1266) (address near3 input) and (redundant with defect$3)
(170) ((address near3 input) and (redundant with defect$3)) and
(198) (((address near3 input) and (redundant with defect$3)) and
(31) (((address near3 input) and (redundant with defect$3)) and
(144) ((address near2 input) near2 (circuit signal)) and redundant
(1) (defect$3 near3 address) near3 stor$3
(1) defect$3 with stor$3) and redundan$2
(7) defect$3 with stor$3
(1) (defect$3 near3 address) and redundan$2
(67880) memrv and redundan$2

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DB: USPAT:US FGPUB:EPG:JPG:DERWENT:BM:108

Default display: OR

☒ Detail ☒ Highlight all hit items ready

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(((memory and redundan$2) and ((defect$3 adj3 address) near3 stor$3)) and
(redundan$2 adj2 decoder)) and (subblock sub-block)) and (defect$3 near3
stor$3 near3 circuit)]
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	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	Z	3	2
1			US 20030031058 A1	20030213	165	Semiconductor device formed in a rectangle region on a	365/189.09	257/E23.02; 365/51		Kajigaya, Kazuhiko et al.						
2			US 20020054514 A1	20020509	168	Semiconductor memory device and defect remedying method	365/189.02	257/E23.02		Kajigaya, Kazuhiko et al.						
3			US 6657901 B2	20031202	162	Semiconductor device formed in a rectangle region on a	365/189.02	257/E23.02; 365/51;		Kajigaya, Kazuhiko et al.						
4			US 6515913 B2	20030204	160	Semiconductor memory device and defect remedying method	365/189.02	257/E23.02; 365/230.02;		Kajigaya, Kazuhiko et al.						
5			US 6335884 B1	20020101	159	Semiconductor memory device and defect remedying method	365/189.02	257/E23.02; 365/230.02;		Kajigaya, Kazuhiko et al.						
6			US 6212089 B1	20010403	161	Semiconductor memory device and defect remedying method	365/51	257/E23.02; 365/189.01;		Kajigaya, Kazuhiko et al.						
7			US 6178127 B1	20010123	33	Semiconductor memory device allowing reliable repairing	365/200	365/230.03		Haraguchi, Yoshiyuki						
8			US 6160744 A	20001212	162	Semiconductor memory device and defect remedying method	365/200	365/189.02; 365/230.03;		Kajigaya, Kazuhiko et al.						
9			US 6049500 A	20000411	160	Semiconductor memory device and defect remedying method	365/230.02	257/E23.02; 365/230.03;		Kajigaya, Kazuhiko et al.						
10			US 5995422 A	19991130	10	Redundancy circuit and method of a semiconductor	365/200	365/225.7		Im, Heung-Soo et al.						
11			US 5854508 A	19981229	161	Semiconductor memory device having zigzag bonding pad	257/786	257/666; 257/784;		Kajigaya, Kazuhiko et al.						
12			US 5602771 A	19970211	160	Semiconductor memory device and defect remedying method	365/51	257/E23.02; 365/230.03;		Kajigaya, Kazuhiko et al.						